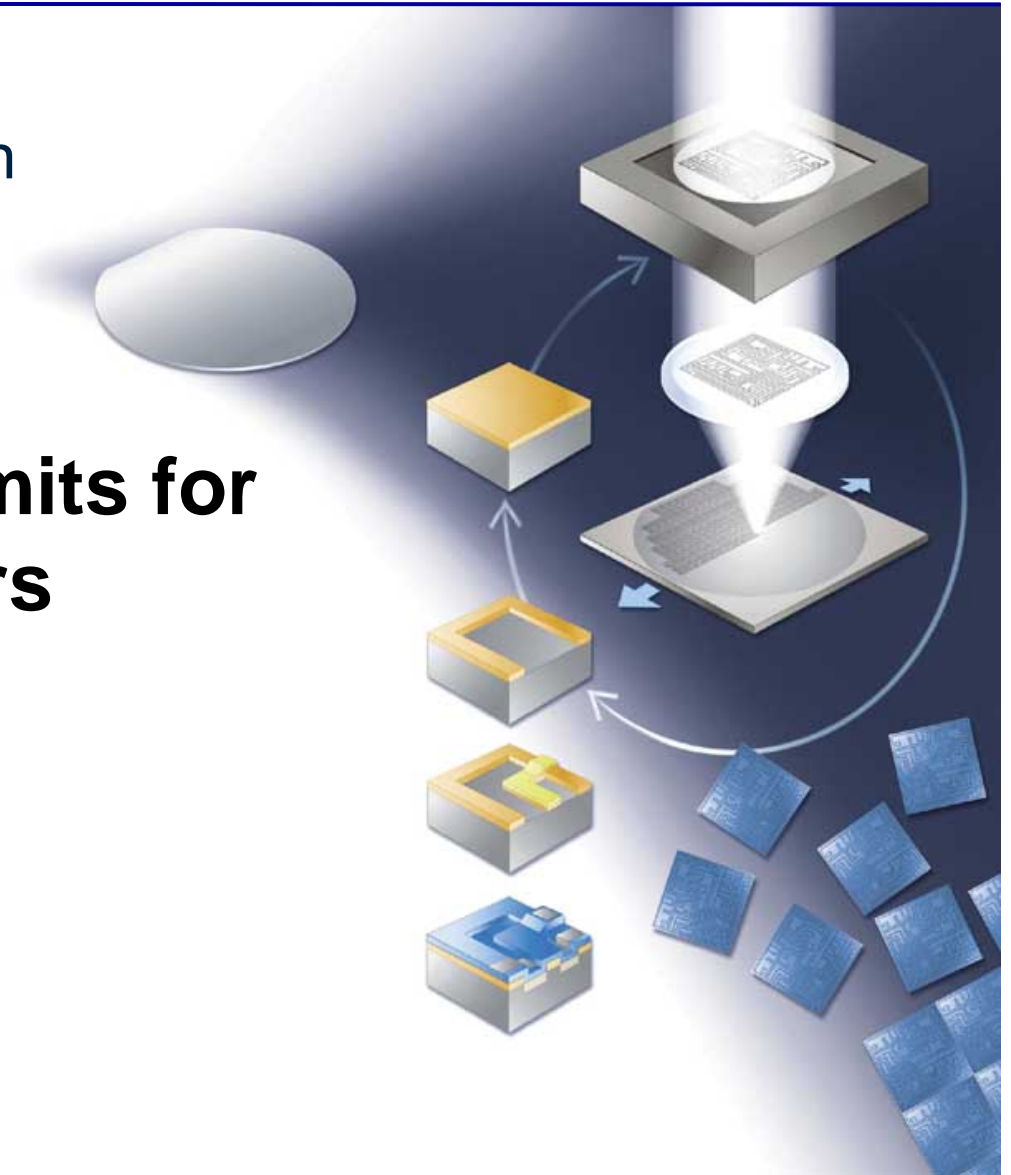


Lithography Optics Division

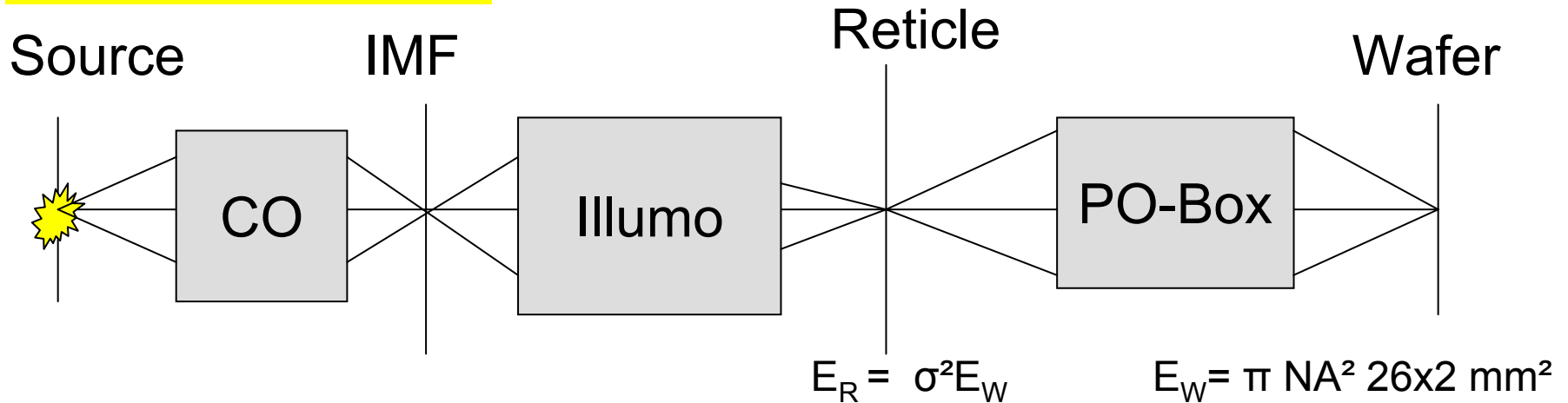
Optical Design Limits for EUV scanners

Peter Kürz



Etendue within EUVL system

$$E_{\text{etendue}} = \pi \text{NA}^2 A$$



Source diameter for source etendue of 3 mm^2 and two collection angles:

NA \ σ	0.8	0.9	collection angle / °	max. source diameter / mm
0.25	6.5	0.9	50	1.4
0.35	12.8	1.0	70	1.2

$E = 3 \text{ mm}^2 \text{ sr}$ is a good etendue target for the source

higher etendue can be used in some settings

Throughput optimization process

- Optimal case:
 - source power maximized for minimized source size
 - sufficiently small etendue for all settings
 - no design restrictions to optical train
 - „Large source“ case:
 - source power maximized for larger source size
 - light loss due to too large source etendue for some settings
 - throughput optimization
 - identify most important settings for which system throughput should be optimal
 - find source and collection parameters to maximize throughput for most important settings
 - minimize light loss for other settings
- ⇒ close collaboration between source and optics suppliers needed

Günther Derra and Wolfgang Singer: Collection efficiency of EUV sources; SPIE 2003